Corrigendum-influence of excitation power on temperature-dependent photoluminescence of phase-separated InGaN quantum wells

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The authors would like to apologize for omitting “Acknowledgement” in the paper on Chinese Optics Letters vol. 14, no. 4, page 042302. The “Acknowledgement” for the paper is as follows: This work was supported by the Specialized Research Fund for the Doctoral Program of Higher Education of China (No. 20120131110006), the Key Science and Technology Program of Shandong Province, China (No. 2013GGX10221), the Key Laboratory of Functional Crystal Materials and Device (Shandong University, Ministry of Education) (No. JG1401), the National Natural Science Foundation of China (No. 61306113), and the Major Research Plan of the National Natural Science Foundation of China (No. 91433112).

doi: 10.3788/COL201614.083501.

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